

Thyristor Surge Suppressors (TSS) Data Sheet

Description

DO-214AA Thyristor solid state protection thyristor protect telecommunications equipment such as modems, line cards, fax machines, and other CPE.

P Series devices are used to enable equipment to meet various regulatory requirements including GR 1089, ITU K.20, K.21 and K.45, IEC 60950, UL 60950, and TIA-968 (formerly known as FCC Part 68).



Features

Compared to surge suppression using other technologies, P Series devices offer absolute surge protection regardless of the surge current available and the rate of applied voltage (dv/dt). P Series devices:

- Cannot be damaged by voltage
- Eliminate hysteresis and heat dissipation typically found with clamping devices
- Eliminate voltage overshoot caused by fast-rising transients
- Are non-degenerative
- Will not fatigue
- Have low capacitance, making them ideal for high-speed transmission equipment
- Meets MSL level 1, per J-STD-020
- Safety certification: UL: E244458

Electrical Parameters

Parameter	Definition
V_{DRM}	Peak Off-state Voltage – maximum voltage that can be applied while maintaining off state
V_{S}	Switching Voltage – maximum voltage prior to switching to on state
V_{T}	On-state Voltage – maximum voltage measured at rated on-state current
I_{DRM}	Leakage Current – maximum peak off-state current measured at V_{DRM}
I_{S}	Switching Current – maximum current required to switch to on state
I_{T}	On-state Current – maximum rated continuous on-state current
I_{H}	Holding Current – minimum current required to maintain on state
C_{O}	Off-state Capacitance – typical capacitance measured in off state
V_{PP}	Peak Pulse Voltage – maximum rated peak impulse voltage
I_{PP}	Peak Pulse Current – maximum rated peak impulse current

Electrical Characteristics

Part Number	V_{DRM} (V)	V_S (V)	V_T (V)	I_{DRM} (μ A)	I_S (mA)	I_T (A)	I_H (mA)	C_O (pF)	V_{PP} 10/700 μ s (V)	I_{PP} 10/1000 μ s (A)	Marking
P0080SA	6	25	4	5	800	2.2	50	50	2000	45	P008A
P0080SB	6	25	4	5	800	2.2	50	70	4000	80	P008B
P0080SC	6	25	4	5	800	2.2	50	100	6000	100	P008C
P0300SA	25	40	4	5	800	2.2	50	70	2000	45	P03A
P0300SB	25	40	4	5	800	2.2	50	70	4000	80	P03B
P0300SC	25	40	4	5	800	2.2	50	100	6000	100	P03C
P0640SA	58	77	4	5	800	2.2	150	50	2000	45	P06A
P0640SB	58	77	4	5	800	2.2	150	60	4000	80	P06B
P0640SC	58	77	4	5	800	2.2	150	100	6000	100	P06C
P0720SA	65	88	4	5	800	2.2	150	50	2000	45	P07A
P0720SB	65	88	4	5	800	2.2	150	60	4000	80	P07B
P0720SC	65	88	4	5	800	2.2	150	100	6000	100	P07C
P0900SA	75	98	4	5	800	2.2	150	45	2000	45	P09A
P0900SB	75	98	4	5	800	2.2	150	55	4000	80	P09B
P0900SC	75	98	4	5	800	2.2	150	90	6000	100	P09C
P1100SA	90	130	4	5	800	2.2	150	45	2000	45	P11A
P1100SB	90	130	4	5	800	2.2	150	55	4000	80	P11B
P1100SC	90	130	4	5	800	2.2	150	90	6000	100	P11C
P1300SA	120	160	4	5	800	2.2	150	45	2000	45	P13A
P1300SB	120	160	4	5	800	2.2	150	55	4000	80	P13B
P1300SC	120	160	4	5	800	2.2	150	90	6000	100	P13C
P1500SA	140	180	4	5	800	2.2	150	40	2000	45	P15A
P1500SB	140	180	4	5	800	2.2	150	60	4000	80	P15B
P1500SC	140	180	4	5	800	2.2	150	85	6000	100	P15C
P1800SA	170	220	4	5	800	2.2	150	40	2000	45	P18A
P1800SB	170	220	4	5	800	2.2	150	60	4000	80	P18B
P1800SC	170	220	4	5	800	2.2	150	85	6000	100	P18C
P2300SA	190	260	4	5	800	2.2	150	35	2000	45	P23A
P2300SB	190	260	4	5	800	2.2	150	55	4000	80	P23B
P2300SC	190	260	4	5	800	2.2	150	80	6000	100	P23C

Electrical Characteristics

Part Number	V_{DRM} (V)	V_S (V)	V_T (V)	I_{DRM} (μ A)	I_S (mA)	I_T (A)	I_H (mA)	C_O (pF)	V_{PP} 10/700 μ s (V)	I_{PP} 10/1000 μ s (A)	Marking
P2600SA	220	300	4	5	800	2.2	150	35	2000	45	P26A
P2600SB	220	300	4	5	800	2.2	150	50	4000	80	P26B
P2600SC	220	300	4	5	800	2.2	150	80	6000	100	P26C
P3100SA	275	350	4	5	800	2.2	150	30	2000	45	P31A
P3100SB	275	350	4	5	800	2.2	150	45	4000	80	P31B
P3100SC	275	350	4	5	800	2.2	150	65	6000	100	P31C
P3500SA	320	400	4	5	800	2.2	150	30	2000	45	P35A
P3500SB	320	400	4	5	800	2.2	150	40	4000	80	P35B
P3500SC	320	400	4	5	800	2.2	150	65	6000	100	P35C

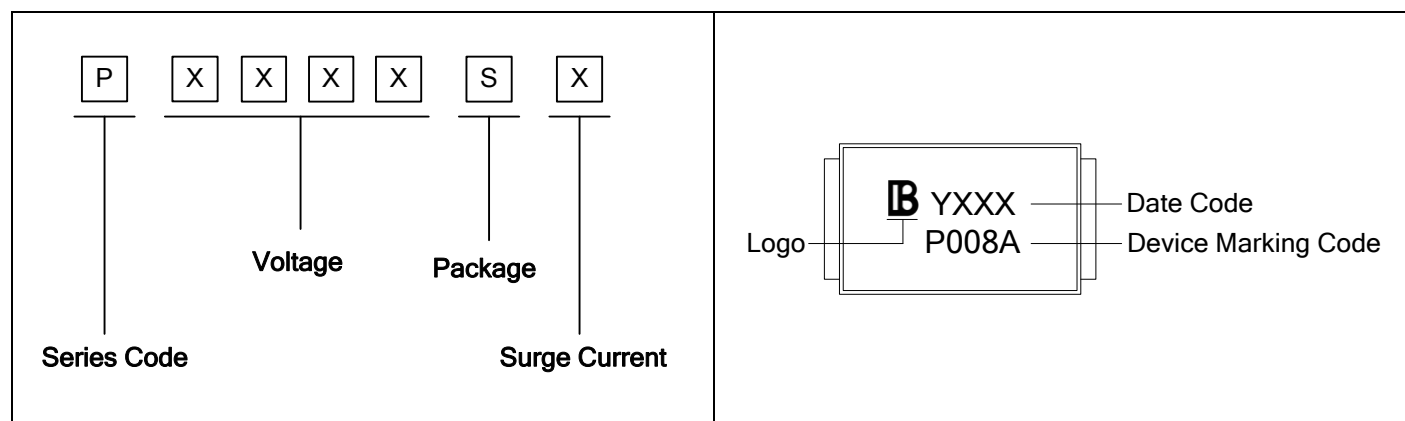
Notes:

- All measurements are made at an ambient temperature of 25°C. I_{PP} applies to -40°C through +85°C temperature range.
- Off-state capacitance(C_O) is measured at 1 MHz with a 2V bias and is typical value.

Thermal Considerations

Package DO-214AA/SMB	Symbol	Parameter	Value	Unit
	T_J	Operating Junction Temperature	-40 to +150	°C
	T_S	Storage Temperature Range	-40 to +150	°C
	$R_{\theta JA}$	Junction to Ambient on printed circuit	90	°C/W

Part Number Code and Marking



Characteristics Curves

Figure 1. V-I Characteristics

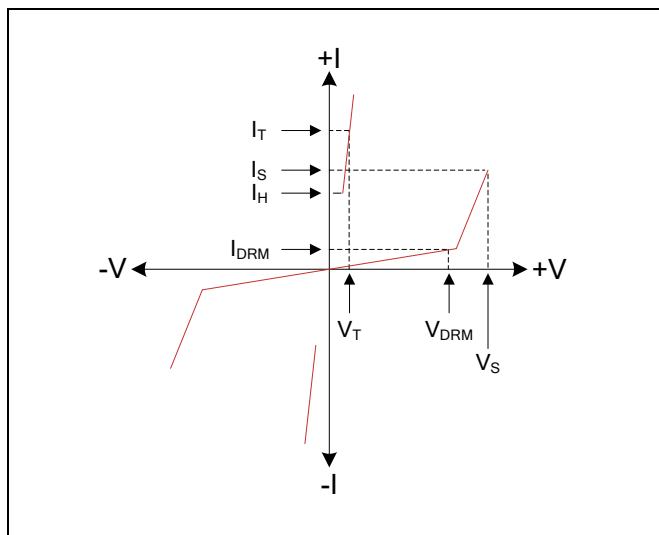


Figure 2. $t_r \times t_d$ Pulse Wave-form

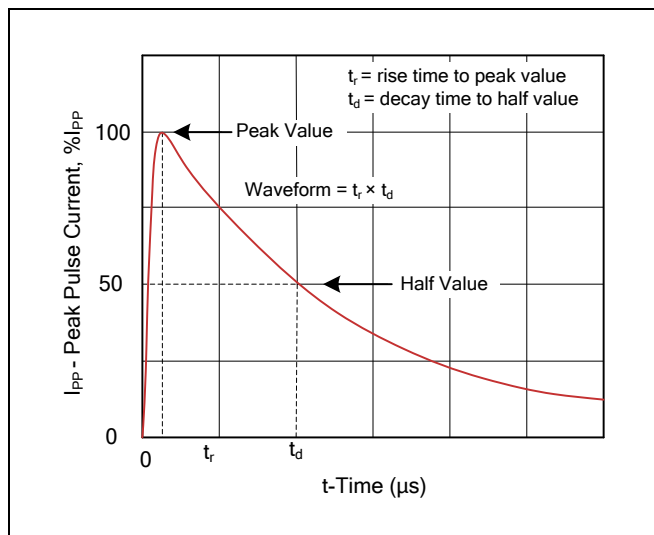


Figure 3. Normalized V_S Change versus Junction Temperature

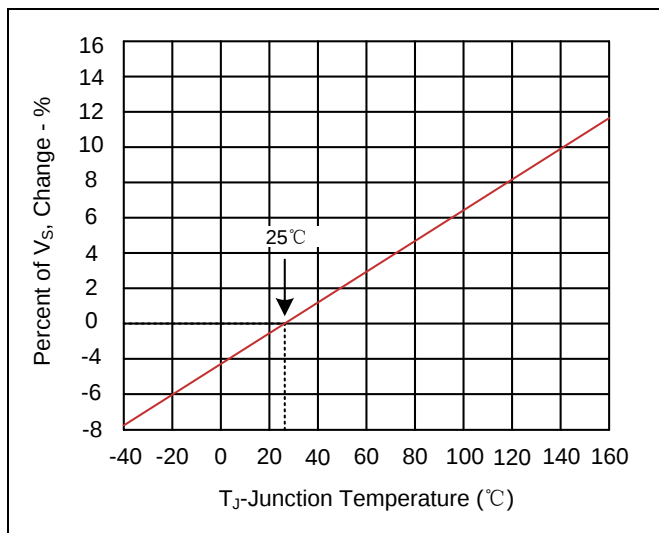
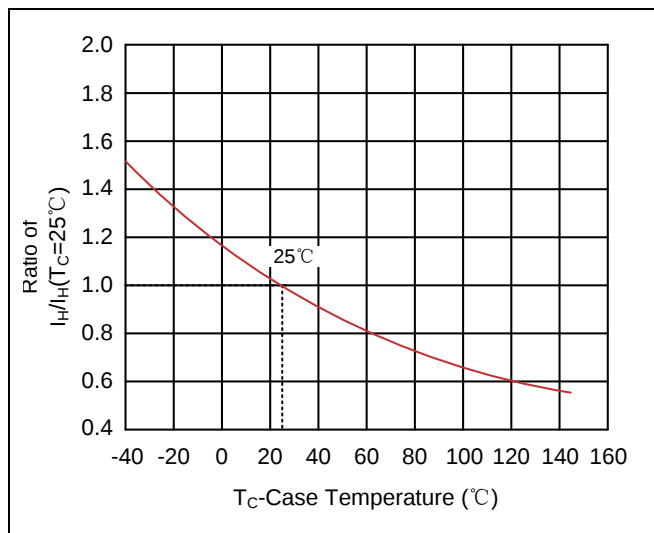
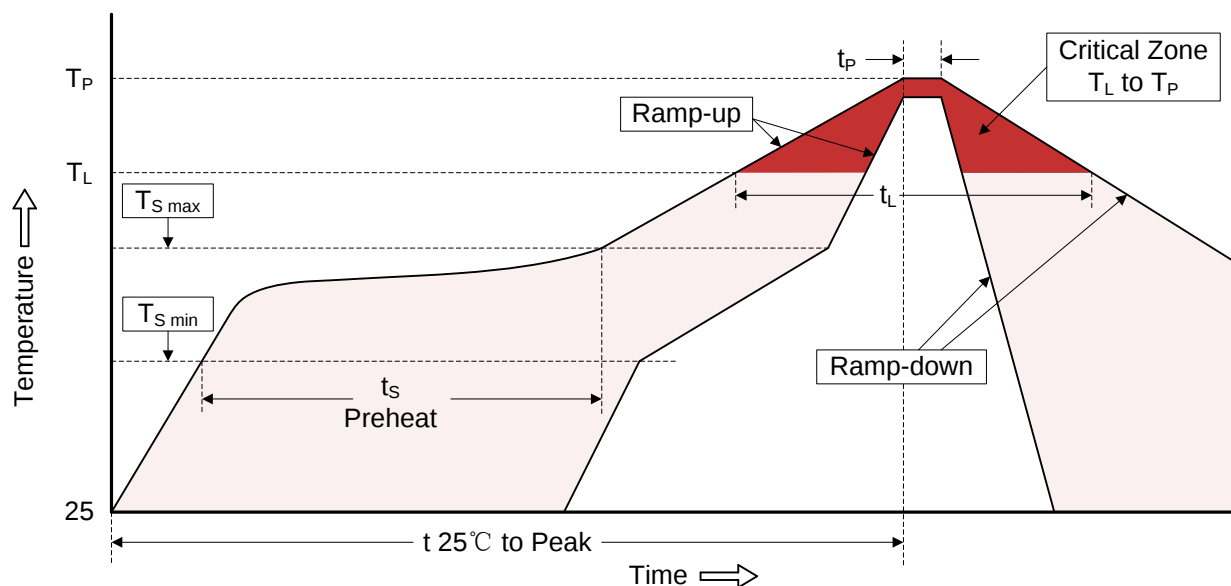


Figure 4. Normalized DC Holding Current versus Case Temperature



Recommended Soldering Conditions

Reflow Soldering



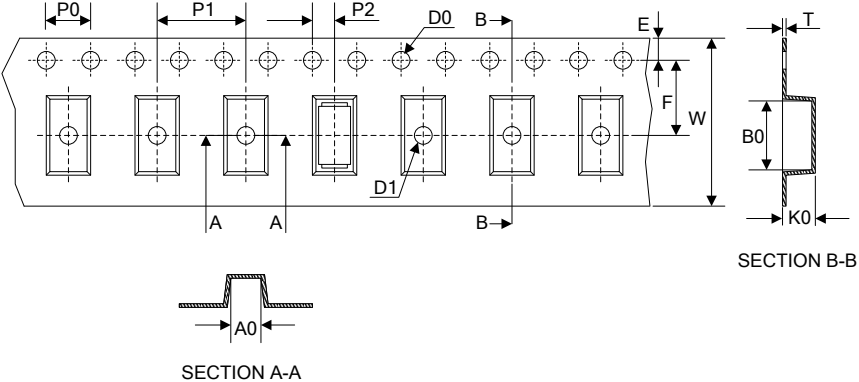
Recommended Conditions

Profile Feature	Pb-Free Assembly
Average ramp-up rate (T _L to T _P)	3°C/second max.
Preheat	
-Temperature Min (T _{S min})	150°C
-Temperature Max (T _{S max})	200°C
-Time (min to max) (t _s)	60-180 seconds
T _{S max} to T _L	
-Ramp-up Rate	3°C/second max.
Time maintained above:	
-Temperature (T _L)	217°C
-Time (t _L)	60-150 seconds
Peak Temperature (T _P)	260°C
Time within 5°C of actual Peak Temperature (t _p)	20-40 seconds
Ramp-down Rate	6°C/second max.
Time 25°C to Peak Temperature	8 minutes max.

Dimensions (SMB/DO-214AA)

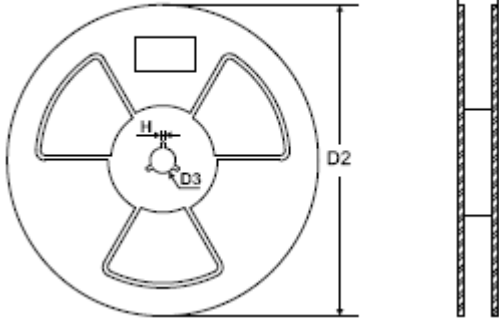
Symbol	Millimeters		Inches	
	Min.	Max.	Min.	Max.
L	4.22	4.70	0.166	0.185
D	3.40	3.94	0.134	0.155
D1	1.90	2.20	0.075	0.086
T	5.21	5.59	0.205	0.220
T1	0.91	1.42	0.036	0.056
d	0.05	0.20	0.002	0.008
H	1.95	2.40	0.077	0.095

Packaging

Tape		Symbol	Dimension (mm)
		W	12.00±0.30
		P0	4.00±0.10
		P1	8.00±0.10
		P2	2.00±0.10
		D0	Φ1.55±0.05
		D1	Φ1.55±0.05
		E	1.75±0.10
		F	5.50±0.10
		A0	3.76±0.10
		B0	5.69±0.10
		K0	2.70±0.10
		T	0.25±0.10
Reel		D2	Φ330.0±2.0
		D3	Φ13.5±0.5
		H	2.5±0.5
		W1	16.0±1.0

THYRISTOR SURGE SUPPRESSORS

PXXXXSX

	Quantity: 2500PCS P0080SB: 3000PCS
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